EAST Search History (24/pp)

			•	1-9//		
Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	((konno near1 taichiroo).in. (arai near1 masahiro).in. hitachi.as.) and (exfoliati\$2).clm. and (transparent near3 conductive).clm. and clad\$4. clm. and active.clm. and (un\$1doped non\$1doped).clm. and light\$1emitting adj (device element diode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/26 10:16
L2		((konno near1 taichiroo).in. (arai near1 masahiro).in. hitachi.as.) and (alumin\$1um Al adhes\$3 exfoliat\$3). clm. and (transparent near3 conductive).clm. and clad\$4.clm. and active.clm. and (un\$1doped non\$1doped).clm. and (light adj emitting adj (device element diode)). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/26 10:17
L3	0	((konno near1 taichiroo).in. (arai near1 masahiro).in. hitachi.as.) and (alumin\$1um Al adhes\$3 exfoliat\$3). clm. and (transparent near3 conductive).clm. and clad\$4.clm. and active.clm. and (undoped nondoped non-doped un-doped).clm. and (light adj emitting adj (device element diode)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/26 10:18
L4	0	((konno near1 taichiroo).in. (arai near1 masahiro).in. hitachi.as.) and (alumin\$1um Al adhes\$3 exfoliat\$3). clm. and (transparent near3 conductive).clm. and clad\$4.clm. and active.clm. and (doped undoped nondoped non-doped un-doped).clm. and (light adj emitting adj (device element diode)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/26 10:18
L5	!	(257/79.ccls. 257/8\$1.ccls. 257/9\$1. ccls. 257/100.ccls. 257/101.ccls. 257/102.ccls. 257/103.ccls. 372/43.01. ccls. 372/45.01.ccls.) and (alumin\$1um Al adhes\$3 exfoliat\$3) and (transparent near3 conductive) and clad\$4 and active and (doped undoped nondoped non-doped un-doped) and (light adj emitting adj (device element diode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/26 10:21

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L6	101	(257/79.ccls. 257/8\$1.ccls. 257/9\$1. ccls. 257/100.ccls. 257/101.ccls. 257/102.ccls. 257/103.ccls. 372/43.01. ccls. 372/45.01.ccls.) and (alumin\$1um Al adhes\$3 exfoliat\$3) and (transparent near3 conductive) and clad\$4 and active and (doped undoped nondoped non-doped un-doped) and (light adj emitting adj (device element diode)) and @ad<"20040325"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/26 10:21
S1	5	"807413".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/26 07:53
S2	2	jp-2002226846\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/30 19:06
S3	41	exfoliati\$2.ti,ab,clm. and (light-emitting adj (device diode) light adj emitting adj (device diode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:12
S4	3	exfoliati\$2.ti,ab,clm. and (light-emitting adj (device diode) light adj emitting adj (device diode)) and AlGaAs and (ITO indium-tin-oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR ·	ON	2005/05/30 19:20
<b>S</b> 5	1	exfoliati\$2 near6 AlGaAs and (ITO indium-tin-oxide) and (257/79.ccls. 257/8\$1.ccls. 257/9\$1.ccls. 257/10\$1. ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:22
· S6	1	exfoliati\$2 near6 AlGaAs and (ITO indium-tin-oxide) and (372/4\$1.ccls. 372/50.ccls. 257/79.ccls. 257/8\$1.ccls. 257/9\$1.ccls. 257/10\$1.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:22
<b>S7</b>	2	(lift-off exfoliati\$2) near6 AlGaAs and (ITO indium-tin-oxide) and (372/4\$1. ccls. 372/50.ccls. 257/79.ccls. 257/8\$1.ccls. 257/9\$1.ccls. 257/10\$1. ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:24
S8	5	(lift-off exfoliati\$2) near6 (aluminum AlGaAs) and (ITO indium-tin-oxide) and (372/4\$1.ccls. 372/50.ccls. 257/79.ccls. 257/8\$1.ccls. 257/9\$1. ccls. 257/10\$1.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:26

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S9	1	(exfoliati\$2) near6 (aluminum AlGaAs)and (372/4\$1.ccls. 372/50. ccls. 257/79.ccls. 257/8\$1.ccls. 257/9\$1.ccls. 257/10\$1.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:26
\$10	1	(exfoliati\$2) near6 (aluminum AlGaAs) and (372/4\$1.ccls. 372/50.ccls. 257/79.ccls. 257/8\$1.ccls. 257/9\$1. ccls. 257/10\$1.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:26
S11	1	(exfoliati\$2) near6 (aluminum AlGaAs Al AlAs) and (372/4\$1.ccls. 372/50. ccls. 257/79.ccls. 257/8\$1.ccls. 257/9\$1.ccls. 257/10\$1.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:27
S12	131	(exfoliati\$2) near6 aluminum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:29
S13	68	(exfoliati\$2) near3 aluminum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON :	2005/05/30 19:34
S14		(ITO indium-tin-oxide) near6 (AlGaAs AlAs) and ((light-emitting light adj emitting) adj (diode device laser))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:03
S15   	1259	stop adj layer.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:49
; S16	2	stop adj layer.ti. and light-emitting adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 19:49
S17	0	(ITO indium-tin-oxide) near6 (AlGaAs:Zn AlGaAs:Si AlGaAs:Ge AlAs:Zn AlAs:Si AlGa:Ge) and ((light-emitting light adj emitting) adj (diode device laser))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2005/05/30 20:04
S18	0	(ITO indium-tin-oxide) near6 ("AlGaAs:Zn" "AlGaAs:Si" "AlGaAs:Ge" "AlAs:Zn" "AlAs:Si" "AlGa:Ge") and ((light-emitting light adj emitting) adj (diode device laser))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:04

S19	0 (ITO indium-tin-oxide) near6 (AlGaAs near4 ((heavily highly) adj doped) "AlGaAs:Zn" "AlGaAs:Si" "AlGaAs:Ge" "AlAs:Zn" "AlAs:Si" "AlGa:Ge") and ((light-emitting light adj emitting) adj (diode device laser))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:05
S20	0 (ITO indium-tin-oxide) near10 (AlGaAs near4 ((heavily highly) adj doped) "AlGaAs:Zn" "AlGaAs:Si" "AlGaAs:Ge" "AlAs:Zn" "AlAs:Si" "AlGa:Ge") and ((light-emitting light adj emitting) adj (diode device laser))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:06
S21	17 (ITO indium-tin-oxide) near10 AlGaAs and (light-emitting light adj emitting) adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:06
S22	0 (ITO indium-tin-oxide) near10 AlGaAs:Zn and (light-emitting light adj emitting) adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:06
S23	1 (ITO indium-tin-oxide) near10 AlGaAs near10 Zn and (light-emitting light adj emitting) adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:07
S24	<ol> <li>(ITO indium-tin-oxide) near10 AlGaAs near10 (Si Ge Zn Mg Cd) and (light-emitting light adj emitting) adj diode</li> </ol>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR .	ON :	2005/05/30 20:08
S25	0 (ITO indium-tin-oxide) near10 AlGaAs near10 heavily adj doped and (light-emitting light adj emitting) adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:08
S26 '	0 (ITO indium-tin-oxide) near10 AlGaAs near10 (n+ "N+" heavily adj doped) and (light-emitting light adj emitting) adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:09
S27	0 (ITO indium-tin-oxide) near10 AlGaAs near10 ("n.sub.+" "N.sub.+" heavily adj doped) and (light-emitting light adj emitting) adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:09

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S28	17	(ITO indium-tin-oxide) near10 AlGaAs and (light-emitting light adj emitting) adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:20
S29	4	ohmic adj contact near10 (AIAs AIGaAs) near10 (ITO TCO transparent) and (light-emitting adj diode light adj emitting adj diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:25
S30	2	ohmic adj contact near10 (AlAs AlGaAs) near10 (electrode) and (light-emitting adj diode light adj emitting adj diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:30
S31	0	ohmic adj contact near10 (AlAs AlGaAs) near10 (ITO TCO)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:31
S32	0	ohmic adj contact near10 (AlAs AlGaAs) near10 zinc adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:31
S33	106	ohmic adj contact near5 (AlAs AlGaAs)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:32
S34	51	ohmic adj contact near3 (AlAs AlGaAs)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:51
S35		ohmic adj contact near3 (AlAs AlGaAs) and exfoliat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:43
S36	0	(adhesion adhesive) near10 (AlAs AlGaAs) near10 ohmic adj contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 20:51
S37	5	ohmic adj contact near3 (AlAs AlGaAs) and "10.sup.19"\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 21:27

3/26/07 10:24:03 AM

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S38	53	band adj gap near4 ohmic adj contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 21:54
S39 .	27	band adj gap near3 ITO	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 21:47
S40	0	direct adj gap near3 ohmic adj contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 21:49
S41	0	direct adj gap near3 contact adj region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 21:50
: S42		direct adj2 gap near3 contact adj region	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 21:50
S43 :	6	contact adj resistance near4 band adj gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:00
S44	Ó	(p-type adj ito) near5 (band adj gap)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:06
S45	0	"Al.sub."\$4"Ga.sub."\$4As near10 band adj gap near10 (contact adj region ohmic adj contact)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:15
S46	2	"6236065".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:35
S47	2	"6495862".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:35

S48	0	"6495862".pn. and AlGaN	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:35
S49	, 1	"6495862".pn. and exfoliat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:37
S50 :	1	"6495862".pn. and exfoliat\$3 and (AlGaAs AlGaN Al aluminum)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:50
S51	690	contact adj (region layer) near6 (impurity adj concentration)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:51
S52	22	contact adj (region layer) near4 (impurity adj concentration) and transparent adj electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 22:51
S53	0	direct adj2 band adj gap near10 (ohmic adj contact contact adj region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	; ON	2005/05/31 06:43
\$54	6	"Al.sub."\$4"Ga.sub."\$4As near10 (ohmic adj contact contact adj region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/31 06:43
S55		(US-20020096688-\$ or US-20020110940-\$ or US-20040197981-\$ or US-20040227151-\$).did. or (US-5770489-\$ or US-6055262-\$ or US-6856087-\$ or US-6867426-\$).did. or (JP-2002226846-\$).did. or (JP-2002226846-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/05/31 07:31
S56	3	S55 and Zn	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/31 07:19

S57	2	S55 and Mg	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/31 07:20
S58	9	"6495862"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/31 07:21
S59	2	("6495862").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/31 07:21
\$ S60	11	(US-20020096688-\$ or US-20020110940-\$ or US-20040197981-\$ or US-20040227151-\$).did. or (US-5770489-\$ or US-6055262-\$ or US-6856087-\$ or US-6867426-\$ or US-6495862-\$).did. or (JP-2002226846-\$).did. or (JP-2002226846-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/05/31 07:31
S61	1	S60 and autodoped	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/31 07:33
S62	75	autodoped	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/31 07:33
S63	35	autodoped.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF,	2005/05/31 07:33
. S64		jp-1130810\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/01 15:09
\$65 :	2	jp-11307810\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/01 15:09

. S66	2	jp-2002344017\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/01 15:10
S67	2	("6350997").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/01 15:10
S68	2	"6350997".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/07 16:28
S69	3	"116324".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/08 09:42
S70	1	(US-20040227151-\$).did.	US-PGPUB	OR	OFF	2005/11/13 18:03
, <b>S71</b>	1	S70 and prevent\$3 near6 concentrat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/13 18:06
S72	2	("5869849").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/13 18:10
S73	8	JP-2002232005\$-\$.did. JP-2000174344\$-\$.did. JP-08097467\$-\$.did. JP-2000312028\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 18:38
S74	2	jp-2003158887\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 19:11
S75	418	graded near3 clad\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/13 19:34

\$76	6	(double graded) near3 clad\$4 and (indium adj tin adj oxide ito) and (zn zinc) near2 dop\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 19:42
S77	10	(double graded) near2 active and (indium adj tin adj oxide ito) and (zn zinc) near2 dop\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 19:54
S78	10	(double graded bi-layer) near2 active and (indium adj tin adj oxide ito) and (zn zinc) near2 dop\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 19:54
S79	16	(double graded bi-layer laminate) near2 active and (indium adj tin adj oxide ito) and (zn zinc) near2 dop\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 19:55
S80	3	(double graded bi-layer laminate) near2 active and (indium adj tin adj oxide ito) and (zn zinc) near2 dop\$3 and AlGaInP	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 20:29
; S81	, 0	"5869849".pn. and (mqw multiple ad adj "well")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 20:30
S82 -	.1854	(AlGaInP GaAlInP InGaAlP InAlGaP) and (mqw multiple ad adj "well")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 20:31
S83	348	(AlGaInP GaAlInP InGaAlP InAlGaP) with (mqw multiple ad adj "well")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2005/11/13 20:31
, S84	29	(AlGaInP GaAlInP InGaAlP InAlGaP) with (mqw multiple ad adj "well") and ito	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 20:31
S85	6	(AlGaInP GaAlInP InGaAlP InAlGaP) with (mqw multiple ad adj "well") and ito and (zn zinc) near3 dop\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 21:03

		EAST Search	HISTORY			
S86	134	(mqw multiple ad adj "well") with quantum adj2 efficiency	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 21:04
S87		(mqw multiple ad adj "well") with quantum adj2 efficiency with light-emitting adj diode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 21:04
S88	14	(mqw multiple ad adj "well") with quantum adj2 efficiency with (light adj emitting light-emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 21:05
S89	3	(mqw multiple adj "well") with quantum adj2 efficiency with (light adj emitting light-emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 21:05
\$90 !	4	(mqw multiple adj quantum adj "well") with quantum adj2 efficiency with (light adj emitting light-emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/13 21:05
S91	117	MQW near6 efficiency	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 08:58
S92	0	MQW near6 efficiency near6 light adj emitting and LED.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 08:58
· S93	7	MQW near6 efficiency near6 light adj emitting	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 08:58
S94	20	MQW near6 efficiency near6 ("LED" light adj emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 09:49
S95	11454	((257/79) or (257/8\$1) or (257/9\$1) or (257/100) or (257/101) or (257/102) or (257/103)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/14 09:49

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•	S96	12220	((257/79) or (257/8\$1) or (257/9\$1) or (257/100) or (257/101) or (257/102) or (257/103) or (372/43. 01)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/14 09:49
	S97	124	S96 and (damag\$3 exfoliat\$3 degradat\$3 erosion eroding corrosion corroding) near6 electrode and transparent near4 electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 09:52
:	S98	83 ! :	S96 and (damag\$3 exfoliat\$3 degradat\$3 erosion eroding corrosion corroding) near6 electrode and transparent near4 electrode and @ad<"20030401"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 09:52
	S99	1	(US-20040227151-\$).did.	US-PGPUB	OR	OFF	2006/01/26 16:21
	S10 0	. 1	(US-20040227151-\$).did. and "between" and (band adj gap gap)	US-PGPUB	OR	OFF	2006/01/26 16:22
	S10 1	· 2	("5869849").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/06 12:02
	S10 2	2	("20020104997").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/06 12:14
* * * * * * * * * * * * * * * * * * * *	S10 3	81	waveguide adj layer near6 (clad cladding) and (257/8\$1.ccls. 257/9\$1.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 12:18
	S10 4	4	(AlGaInP AlInGaP) and (257/8\$1.ccls. 257/9\$1.ccls.) and "undoped" near4 "between" near4 (clad cladding) near4 active	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 14:14
	S10 5		jp-2001015798\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 14:16
	\$10 6	2	jp-2002232005\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	. <b>ON</b>	2006/03/06 14:17

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S10 7	2	jp-2000174344\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 14:20
S10 8		("6350997").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/06 14:21
S10 9	2	jp-11307810\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/06 14:21
S11 0	2	jp-2002344017\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 14:53
S11 1	2	("20020104997").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/06 14:53
S11 2	0	S111 and doped near12 barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/06 14:53
S11 3	0	S111 and undoped near12 barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/06 14:53
S11 4	0	S111 and un-doped near12 barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR .	OFF	2006/03/06 14:54
S11 5	0	S111 and un-doped near12 MQW	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/06 14:54
S11 6	0	S111 and undoped near12 MQW	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/06 14:54

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S11 7	0	S111 and doped near12 MQW	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/06 14:54
S11 8	14398	((257/79) or (257/8\$1) or (257/9\$1) or (257/100) or (257/101) or (257/102) or (257/103) or (372/43. 01) or (372/45.01)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/06 15:44
S11 9	0	S118 and exfoliat\$3.ti,ab,clm. and (spacer barrier).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 15:45
S12 0	1511	S118 and (spacer barrier).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 15:45
S12 1	509	S118 and (spacer barrier).ti,ab,clm. and (clad cladding).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 15:46
S12 2	. 12	S118 and (spacer barrier).ti,ab,clm. and (clad cladding).ti,ab,clm. and (hitachi.as. konno.in.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 15:47
S12 3	10	S118 and (spacer barrier).clm. and (clad cladding).clm. and (hitachi.as. konno.in.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/06 15:47
S12 4	17	"5869849"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/21 00:10
S12 5	2	("5869849").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/21 00:10
S12 6	14336	((257/79) or (257/8\$1) or (257/9\$1) or (257/10\$1)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/21 01:02

			,			
S12 7	9	S126 and exfoliation and transparent near2 electrode and (AlGaInP AlGaAs)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/21 01:04
S12 8	1981	algaas and (algainp alingap)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/21 07:10
S12 9	38	S128 and (current adj spreading) near10 (ohmic adj contact)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 07:11
S13 0	7 :	S128 and (current adj spreading) near10 (ohmic adj contact) and second adj2 (clad cladding)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 07:15
S13 1	3	s S128 and (current adj spreading) near10 (ohmic adj contact) and second adj2 (clad cladding) and (ito transparent) near2 electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON !	2006/08/21 07:25
S13 2	8	tezen.in. and period and Gan	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 07:27
S13 3	0	tezen.in. and period and AlGaAs	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 07:27
S13 4	1	tezen.in. and AlGaAs	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 07:37
S13 5	148	ohmic adj contact near6 undoped	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	• OR	ON	2006/08/21 07:42
S13 6	35	ohmic adj contact near6 undoped and (light-emitting light adj emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 07:45
+				<u>.                                    </u>	• —	

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S13 7	17	ohmic adj contact near6 buried and (light-emitting light adj emitting)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 07:54
S13 8	37	(algaas gaalas) and (algainp gaalinp) and (ito zno transparent) near2 electrode and (257/79.ccls. 257/8\$1. ccls. 257/9\$1.ccls. 257/10\$1.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 07:56
S13 9	23	(algaas gaalas) and (algainp gaalinp) and (ito zno transparent) near2 electrode and (257/79.ccls. 257/8\$1. ccls. 257/9\$1.ccls. 257/10\$1.ccls.) and @ad<"20040425"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 09:19
S14 0	2	("6,631,149").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/21 09:27
S14	0	algaas and algainp and guide adj layer and (transparent ito) near1 electrode and light adj emitting	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/21 09:28
S14 2	171	algaas and algainp and guide adj layer and light adj emitting	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/21 09:28
S14 3	0	algaas and algainp and guide adj layer near3 multilayer and light adj emitting	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/21 09:28
S14 4	171	algaas and algainp and guide adj layer and light adj emitting	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/21 09:29
, S14 5	51	algaas and algainp and guide adj layer with undoped and light adj emitting	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/21 09:35
S14 6	0	algaas and algainp and guide adj layer with undoped and light adj emitting and electrode near1 (transparent ito)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/21 09:33

S14 7		algaas and algainp and guide adj layer with undoped and light adj emitting and current adj spreading	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/21 09:40
S14 8	. 14	algaas and algainp and guide adj layer with undoped and light adj emitting and current adj blocking	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/21 09:42
S14 9	1	algaas and algainp and guide adj layer with undoped and light adj emitting and current adj blocking and electrode near4 (transparent ito)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 10:06
S15 0		algaas and algainp and guide adj layer near8 undoped and light adj emitting and current adj blocking and electrode near4 (transparent ito)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 10:09
S15 1	35	guide adj layer near8 undoped and light adj emitting and current adj blocking	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 10:18
S15 2		guide adj layer near8 undoped near8 "pairs" near8 doped and light adj emitting	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 10:19
S15 3	37	guide adj layer near8 undoped near8 doped and light adj emitting	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 10:19
S15 4	63	guide adj layer near8 undoped near8 doped and (light adj emitting laser)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 10:19
S15 . 5	8	guide adj layer near8 undoped near8 doped and (light adj emitting laser) and (GaAlInP AlGaInP AlInGaP)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 10:34
S15 6	0	guide adj layer near8 (undoped near1 barrier) near8 doped and (light adj emitting laser) and (GaAlInP AlGaInP AlInGaP)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 10:21

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S15 7	0	guide adj layer near8 (undoped near2 barrier) near8 doped and (light adj emitting laser) and (GaAlInP AlGaInP AlInGaP)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 10:21
S15 8	0	guide adj layer near8 undoped near8 doped near8 (pairs period) and (light adj emitting laser)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 10:34
S15 9	63	guide adj layer near8 undoped near8 doped and (light adj emitting laser)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 10:40
S16 0	0	DBR near6 doped near6 undoped and current adj blocking and transparent near2 electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 10:43
S16 1	17	DBR near6 doped near6 undoped	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 10:43
S16 2	11	"6350997"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/21 12:32
S16 3	2	("6350997").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/21 12:32
\$16 4		jp-08097467\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/21 13:11
S16 5	2	("5600158").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/21 13:17
S16 6	0	(mutli-layer\$2 multilayer\$2) near1 (clad cladding) and GaAlInP	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/21 13:18

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S16 7	0	(mutli-layer\$2 multilayer\$2) near1 (clad cladding) and GaAlInPt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/21 13:18
S16 8	0	(multi-layer\$2 multilayer\$2) near1 (clad cladding) and GaAlInPt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF:	2006/08/21 13:18
S16 9	0	(multi-layer\$2 multilayer\$2) near4 (clad cladding) and GaAlInPt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/21 13:18
S17 0	0	(multi-layer\$2 multilayer\$2 laminate) near4 (clad cladding) and GaAlInPt	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/21 13:18
S17 1	1	(multi-layer\$2 multilayer\$2 laminate) near4 (clad cladding) and GaAlInP	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/21 13:20
S17 2	472	(multi-layer\$2 multilayer\$2 laminate) near4 (clad cladding) and (GaAs GaAlInP)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 13:20
S17 3	38	(multi-layer\$2 multilayer\$2 laminate) near4 (clad cladding) and (GaAs GaAlInP) and (ito transparent) near3 electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 13:31
S17	19	(superlattice) near4 (clad cladding) and (GaAs GaAlInP) and (ito transparent) near3 electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 13:31
S17 5	<u>1</u>	(US-20040227151-\$).did.	US-PGPUB	OR	OFF	2006/11/29 09:52
S17 6	1	(US-20040227151-\$).did. and contact	US-PGPUB	OR	ON	2006/11/29 09:52
S17 7	2	"5869849".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	- OR	OFF	2007/03/24 21:35

S17 8	4	(("5856682") or ("20020104997")).PN.	US-PGPUB; USPAT; EPO; JPO;	OR	OFF	2007/03/24 21:45
	!		DERWENT; IBM_TDB			
\$17 9	2659	257/99.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/24 21:45
S18 0	202	S179 and undoped	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/24 21:47
S18 1	13	S179 and undoped near4 contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/24 21:48
S18 2	134	current adj blocking near10 undoped	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/24 22:10
S18 3	1 ;	current adj blocking near10 undoped and ito	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/24 22:11
S18 4	. 6	"512131".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/24 22:12
S18 5	570	(non\$doped undoped insulati\$2) near10 (current adj blocking)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/24 22:13
S18 6	43	(non\$doped undoped insulati\$2) near10 (current adj blocking) and ito	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/24 22:19
S18 7	. 91	(non\$doped undoped insulati\$2) near10 (current adj blocking) and (conductive near1 transparent ito zno azo)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/24 22:20

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S18 8	52	(non\$doped undoped insulati\$2) near10 (current adj blocking) and (conductive near1 transparent ito zno azo)	USPAT	OR	ON	2007/03/24 22:22
S18 9	52	(non\$doped undoped insulati\$2) near10 (current adj blocking) and (conductive near1 transparent ito zno azo) and current adj blocking	USPAT	OR	ON	2007/03/24 22:25
S19 0	1	"6746948".pn. and blocking adj layer	USPAT	OR	ON	2007/03/24 22:33
S19 1	25	light-emitting and blocking adj layer and 257/99.ccls.	USPAT	OR	ON	2007/03/24 22:36
S19 2	9	light-emitting and blocking adj layer and 257/99.ccls. and (GaInN AlGaN GaAlN InGaN InAlN AlInN GaAlInN GaInAlN InGaAlN InAlGaN AlGaInN AlInGaN)	USPAT	OR	ON	2007/03/24 23:01
S19 3	3	light-emitting and blocking adj layer and 257/99.ccls. and (GaInN AlGaN GaAIN InGaN InAIN AlInN GaAIInN GaInAIN InGaAIN InAIGaN AlGaInN AlInGaN) and transparent near4 (electrode oxide)	USPAT	OR	ON	2007/03/24 23:01
S19 4	. 5	krames.in. and current adj blocking	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/24 23:37
S19 5	0	krames.in. and current adj blocking near10 (un\$1doped non\$1doped)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/24 23:38
S19 6	145	current adj blocking near10 (un\$1doped non\$1doped)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/24 23:38
S19 7	84	current adj blocking near10 (un\$1doped non\$1doped)	USPAT	OR	ON	2007/03/24 23:40
S19 8	41	current adj blocking near10 (un\$1doped non\$1doped) and AlGaAs	USPAT	OR	ON	2007/03/25 00:14
S19 9	12	current adj blocking near10 (un\$1doped non\$1doped) and AlGaAs and (transparent ito zno azo)	USPAT	OR	ON	2007/03/25 00:15
S20 0	1	current adj blocking near10 (un\$1doped non\$1doped) and AlGaAs and (vcsel)	USPAT	OR	ON	2007/03/25 00:15

S20	2374	current adj blocking adj layer.ti,ab,	US-PGPUB;	OR	OFF	2007/03/25 11:13
1		clm.	USPAT; EPO; JPO; DERWENT; IBM_TDB			
S20 2	635	current adj blocking adj layer.ti,ab, clm. and ("372"/\$7.ccls. 257/8\$1.ccls. 257/9\$1.ccls.) and (Al alumin\$1um)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/25 11:16
S20 3	589	current adj blocking adj layer.ti,ab, clm. and ("372"/\$7.ccls. 257/8\$1.ccls. 257/9\$1.ccls.) and (Al alumin\$1um) and @ad<"20040325"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/25 12:09
S20   4	2	("5856682").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/25 12:09
S20 5	2	jp-2000174344\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/25 16:16
S20 6	106	current adj blocking and light-emitting.ti,ab,clm. and "257"/\$7. ccls. and @ad<"20020101"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/25 16:17
S20 7		current adj blocking.ti,ab,clm. and light-emitting.ti,ab,clm. and "257"/\$7. ccls. and @ad<"20020101"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/25 16:24
S20 8	10	current adj blocking.ti,ab,clm. and light-emitting.ti,ab,clm. and "257"/\$7. ccls. and @ad<"20020101" and (zno ito transparent adj conductive)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/25 16:26
S20 ;		current adj blocking.ti,ab,clm. and light-emitting.ti,ab,clm. and "257"/\$7. ccls. and @ad<"20020101" and (zno ito transparent adj conductive) and current adj blocking	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/25 16:59
S21 0	10	current adj (window blocking).ti,ab, clm. and light-emitting.ti,ab,clm. and "257"/\$7.ccls. and @ad<"20020101" and (zno ito transparent adj conductive) and current adj blocking	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/25 17:00

S21 1	26	current adj (window blocking) and light-emitting.ti,ab,clm. and "257"/\$7. ccls. and @ad<"20020101" and (zno ito transparent adj conductive) and current adj blocking	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/25 17:01
S21 2	26	current adj (window constriction blocking) and light-emitting.ti,ab,clm. and "257"/\$7.ccls. and @ad<"20020101" and (zno ito transparent adj conductive) and current adj blocking	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/25 17:02
S21 3	29	current adj2 (window constriction blocking) and light-emitting.ti,ab,clm. and "257"/\$7.ccls. and @ad<"20020101" and (zno ito transparent adj conductive)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/25 17:16
S21 4	48	current adj2 (window constriction blocking) and light-emitting adj (diode device) and "257"/\$7.ccls. and @ad<"20020101" and (zno ito transparent adj conductive)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/25 17:55
S21 5	2	("20020176465").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/25 17:51
S21 6		current adj2 (window constriction blocking spreading) and light-emitting adj (diode device) and "257"/\$7.ccls. and @ad<"20020101" and (zno ito transparent adj conductive)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2007/03/25 17:55
S21 7	47	current adj2 (spreading) and light-emitting adj (diode device) and "257"/\$7.ccls. and @ad<"20020101" and (zno ito transparent adj conductive)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/25 17:56
S21 8	14	(current\$1blocking current\$1spreading) near4 (insulati\$2 dielectric) and (current\$1blocking current\$1spreading) and ("257"/\$7. ccls. "438"/\$7.ccls.) and @ad<"20040325"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/26 08:03
\$21 9	3	(current\$1spreading) near4 (insulati\$2 dielectric) and (current\$1blocking current\$1spreading) and ("257"/\$7. ccls. "438"/\$7.ccls.) and @ad<"20040325"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/26 08:08

S22 0	5 (current\$1spreading) near4 (insulati\$2 dielectric) and (current\$1blocking current\$1spreading) and @ad<"20040325"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/26 08:09
S22 1	0 (current\$1spreading) near4 (insulati\$2 dielectric) and (current\$1blocking current\$1spreading) and @ad<"20040325" and ito near6 electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/26 08:10
S22 2	2 (current\$1spreading) near4 (insulati\$2 dielectric) and (current\$1blocking current\$1spreading) and @ad<"20040325" and (transparent zno ito) near6 electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/26 10:13